

## General Purpose Transistors

### FEATURE

- High Voltage:  $V_{CEO} = -50\text{ V}$ .
- Epitaxial planar type.
- NPN complement: 2SC1623
- We declare that the material of product compliance with RoHS requirements.

#### Pb-Free package is available

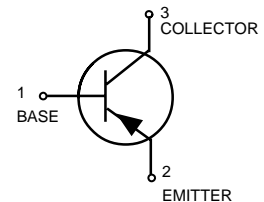
RoHS product for packing code suffix "G"

Halogen free product for packing code suffix "H"



### DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
2SA812QLT1	M8	3000/Tape&Reel
2SA812RLT1	M6	3000/Tape&Reel
2SA812SLT1	M7	3000/Tape&Reel



### MAXIMUM RATINGS

Rating	Symbol	L2SA812	Unit
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Collector-Base Voltage	$V_{CBO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector current-continuoun	$I_c$	-150	mAdc

### THERMAL CHARATEERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A=25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	200 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) $T_A=25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	200 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	$T_j, T_{stg}$	-55 to +150	°C

# General Purpose Transistors

**ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)**

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage ( $I_C = -1\text{mA}$ )	$V_{(BR)CEO}$	-50	-	-	V
Emitter-Base Breakdown Voltage ( $I_E = -50\ \mu\text{A}$ )	$V_{(BR)EBO}$	-6	-	-	V
Collector-Base Breakdown Voltage ( $I_C = -50\ \mu\text{A}$ )	$V_{(BR)CBO}$	-60	-	-	V
Collector Cutoff Current ( $V_{CB} = -50\text{V}$ )	$I_{CBO}$	-	-	-0.1	$\mu\text{A}$
Emitter Cutoff Current ( $V_{BE} = -6\text{V}$ )	$I_{EBO}$	-	-	-0.1	$\mu\text{A}$

**ON CHARACTERISTICS**

DC Current Gain ( $I_C = -1\text{mA}, V_{CE} = -6.0\text{V}$ )	$h_{FE}$	120	-	560	
Collector-Emitter Saturation Voltage ( $I_C = -100\text{mA}, I_B = -10\text{mA}$ )	$V_{CE(sat)}$	-	-0.18	-0.3	V
Base -Emitter On Voltage $I_E = -1.0\text{mA}, V_{CE} = -6.0\text{V}$	$V_{BE}$	-0.58	-0.62	-0.68	V

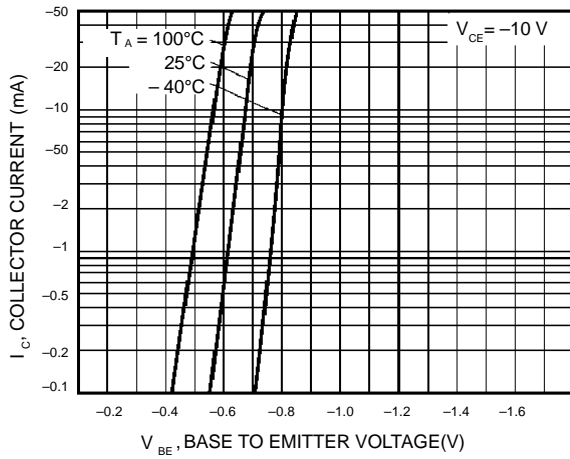
**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $V_{CE} = -6.0\text{V}, I_E = -10\text{mA}$ )	$F_t$	-	180	-	MHz
Output Capacitance ( $V_{CE} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$ )	$C_{obo}$	-	4.5	-	pF

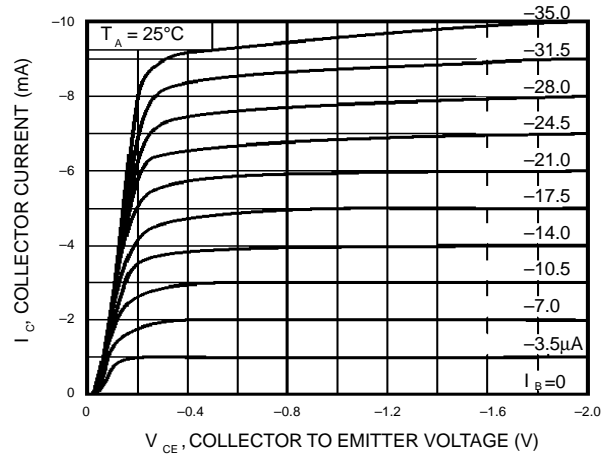
$h_{FE}$  Values are classified as follows

NOTE:	*	Q	R	S
	$h_{FE}$	120~270	180~390	270~560

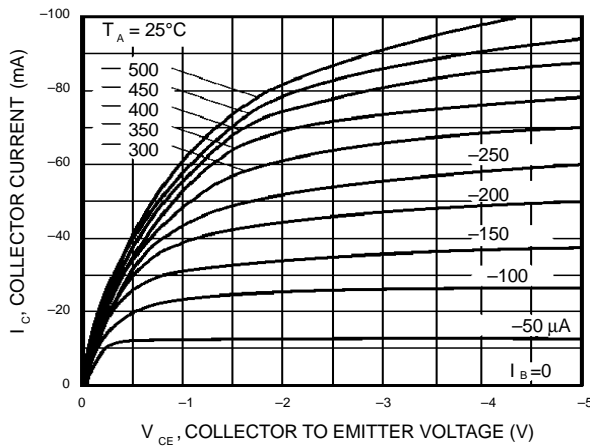
**Fig.1** Grounded emitter propagation characteristics



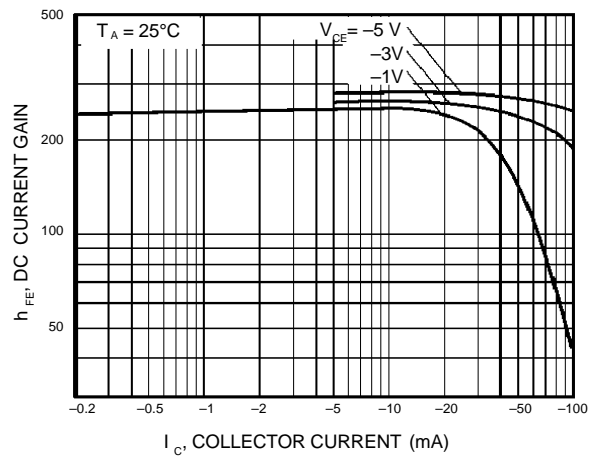
**Fig.2** Grounded emitter output characteristics(I)



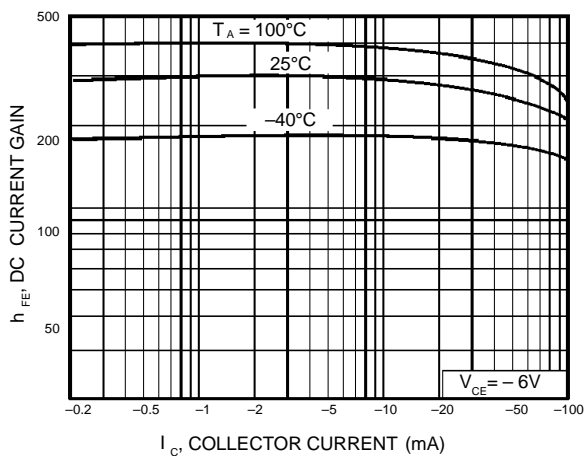
**Fig.3** Grounded emitter output characteristics(II)



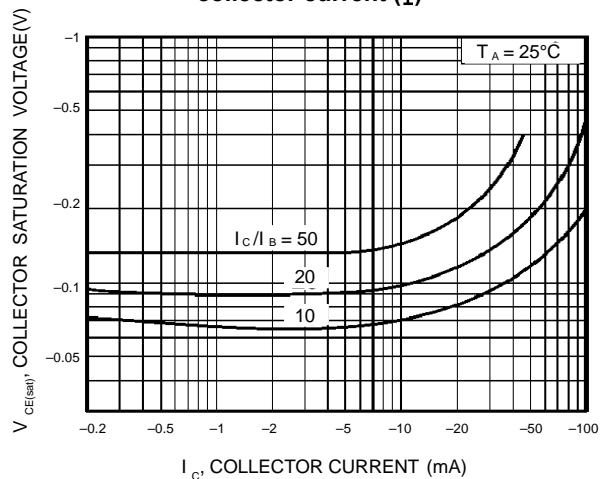
**Fig.4** DC current gain vs. collector current (I)



**Fig.5** DC current gain vs. collector current (II)

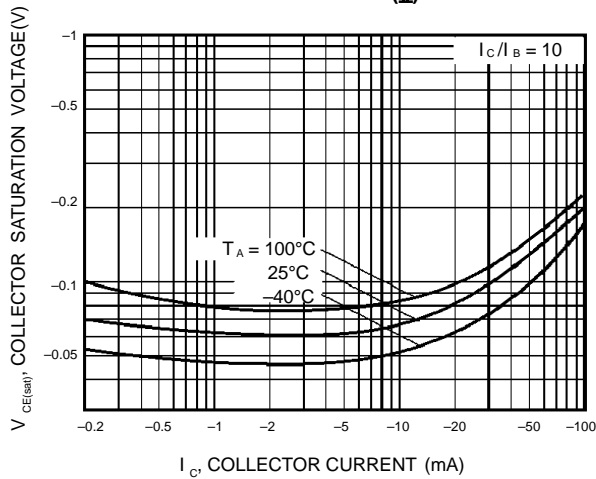


**Fig.6** Collector-emitter saturation voltage vs. collector current (I)

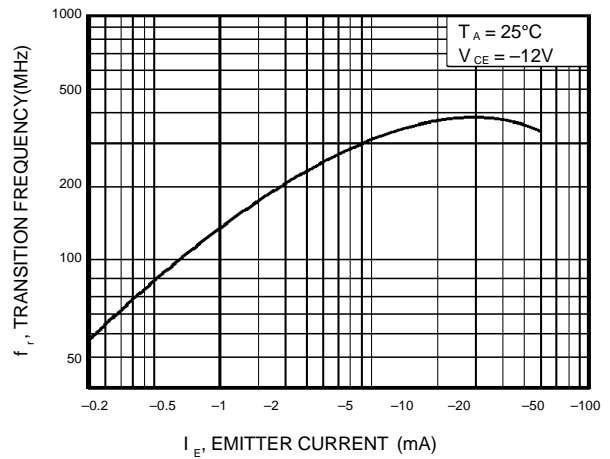


**General Purpose Transistors**

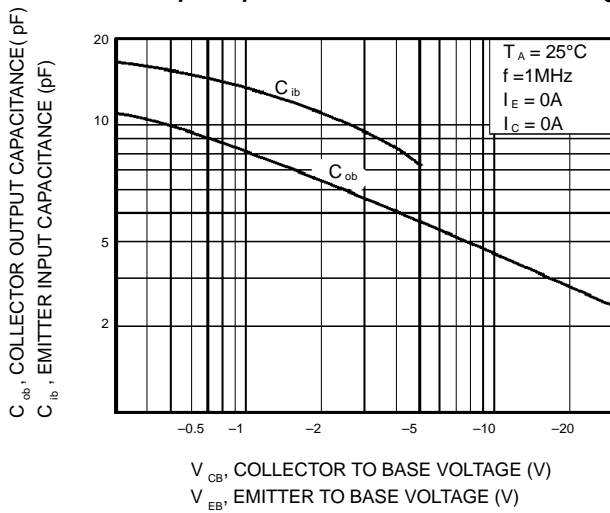
**Fig.7 Collector-emitter saturation voltage vs. collector current (I<sub>c</sub>)**



**Fig.8 Gain bandwidth product vs. emitter current**

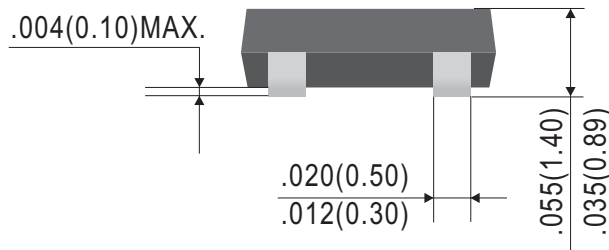
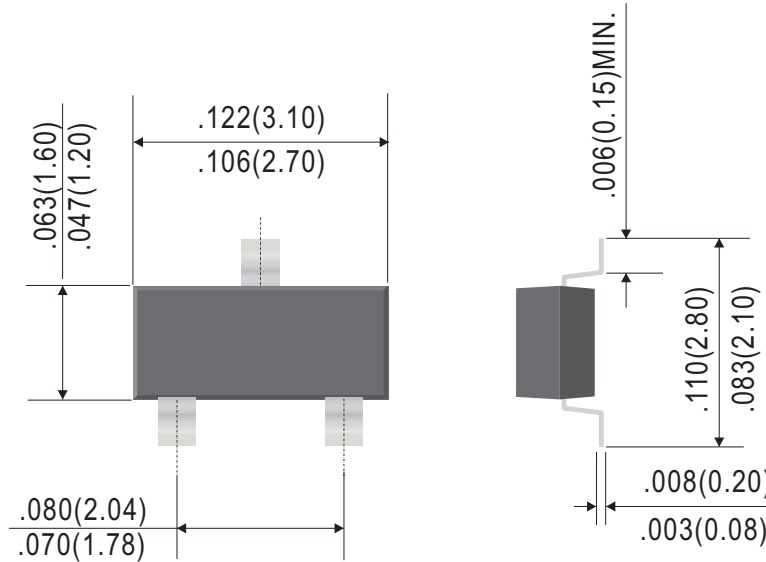


**Fig.9 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage**



**General Purpose Transistors**

**SOT-23**



Dimensions in inches and (millimeters)

